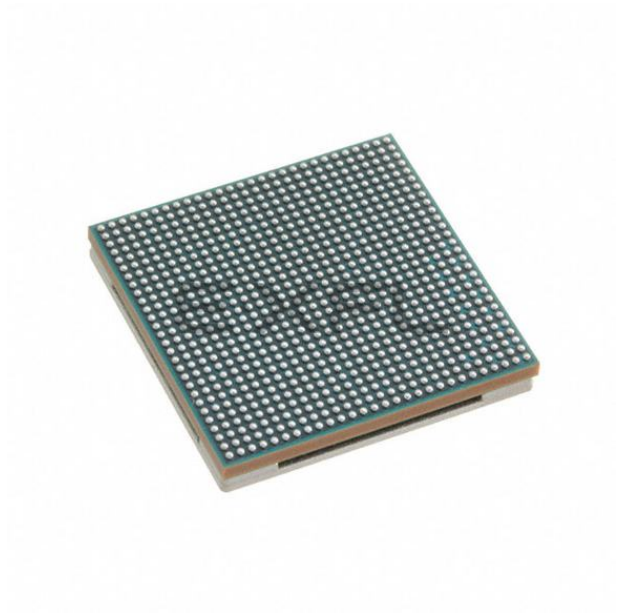

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Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	192000
Total RAM Bits	13619200
Number of I/O	364
Number of Gates	-
Voltage - Supply	0.97V ~ 1.08V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	784-BBGA, FCBGA
Supplier Device Package	784-FCBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/mpf200tls-fcg784i

6.2.1 DC Characteristics over Recommended Operating Conditions

The following table lists the DC characteristics over recommended operating conditions.

Table 5 • DC Characteristics over Recommended Operating Conditions

Parameter	Symbol	Min	Max	Unit	Condition
Input pin capacitance[1]	C_{IN} (dedicated GPIO)		5.6	pf	
	C_{IN} (GPIO)		5.6	pf	
	C_{IN} (HSIO)		2.8	pf	
Input or output leakage current per pin	I_L (GPIO)		10	µA	I/O disabled, high – Z
	I_L (HSIO)		10	µA	I/O disabled, high – Z
Input rise time (10%–90% of V_{DDIx})[2, 3, 4]	T_{RISE}	0.66	2.64	ns	V_{DDIx} = 3.3 V
Input rise time (10%–90% of V_{DDIx})[2, 3, 4]		0.50	2.00	ns	V_{DDIx} = 2.5 V
Input rise time (10%–90% of V_{DDIx})[2, 3, 4]		0.36	1.44	ns	V_{DDIx} = 1.8 V
Input rise time (10%–90% of V_{DDIx})[2, 3, 4]		0.30	1.20	ns	V_{DDIx} = 1.5 V
Input rise time (10%–90% of V_{DDIx})[2, 3, 4]		0.24	0.96	ns	V_{DDIx} = 1.2 V
Input fall time (90%–10% of V_{DDIx})[2, 3, 4]	T_{FALL}	0.66	2.64	ns	V_{DDIx} = 3.3 V
Input fall time (90%–10% of V_{DDIx})[2, 3, 4]		0.50	2.00	ns	V_{DDIx} = 2.5 V
Input fall time (90%–10% of V_{DDIx})[2, 3, 4]		0.36	1.44	ns	V_{DDIx} = 1.8 V
Input fall time (90%–10% of V_{DDIx})[2, 3, 4]		0.30	1.20	ns	V_{DDIx} = 1.5 V
Input fall time (90%–10% of V_{DDIx})[2, 3, 4]		0.24	0.96	ns	V_{DDIx} = 1.2 V
Pad pull-up when V_{IN} = 0[5]	I_{PU}	137	220	µA	V_{DDIx} = 3.3 V
Pad pull-up when V_{IN} = 0[5]		102	166	µA	V_{DDIx} = 2.5 V
Pad pull-up when V_{IN} = 0		68	115	µA	V_{DDIx} = 1.8 V
Pad pull-up when V_{IN} = 0		51	88	µA	V_{DDIx} = 1.5 V
Pad pull-up when V_{IN} = 0[6]		29	73	µA	V_{DDIx} = 1.35 V
Pad pull-up when V_{IN} = 0		16	46	µA	V_{DDIx} = 1.2 V
Pad pull-down when V_{IN} = 3.3 V[5]	I_{PD}	65	187	µA	V_{DDIx} = 3.3 V
Pad pull-down when V_{IN} = 2.5 V[5]		63	160	µA	V_{DDIx} = 2.5 V
Pad pull-down when V_{IN} = 1.8 V		60	117	µA	V_{DDIx} = 1.8 V
Pad pull-down when V_{IN} = 1.5 V		57	95	µA	V_{DDIx} = 1.5 V
Pad pull-down when V_{IN} = 1.35 V		52	86	µA	V_{DDIx} = 1.35 V
Pad pull-down when V_{IN} = 1.2 V		47	79	µA	V_{DDIx} = 1.2 V

1. Represents the die input capacitance at the pad not the package.
2. Voltage ramp must be monotonic.
3. Numbers based on rail-to-rail input signal swing and minimum 1 V/ns and maximum 4 V/ns. These are to be used for input delay measurement consistency.
4. I/O signal standards with smaller than rail-to-rail input swings can use a nominal value of 200 ps 20%–80% of swing and maximum value of 500 ps 20%–80% of swing.
5. GPIO only.

6.2.2 Maximum Allowed Overshoot and Undershoot

During transitions, input signals may overshoot and undershoot the voltage shown in the following table. Input currents must be limited to less than 100 mA per latch-up specifications.

I/O Standard	V_{DDI} Min (V)	V_{DDI} Typ (V)	V_{DDI} Max (V)	V_{IL} Min (V)	V_{IL} Max (V)	V_{IH} Min (V)	V_{IH}[1] Max (V)
SSTL135I	1.283	1.35	1.418	–0.3	V_{REF} – 0.09	V_{REF} + 0.09	1.418
SSTL135II	1.283	1.35	1.418	–0.3	V_{REF} – 0.09	V_{REF} + 0.09	1.418
HSTL15I	1.425	1.5	1.575	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	1.575
HSTL15II	1.425	1.5	1.575	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	1.575
HSTL135I	1.283	1.35	1.418	–0.3	V_{REF} – 0.09	V_{REF} + 0.09	1.418
HSTL135II	1.283	1.35	1.418	–0.3	V_{REF} – 0.09	V_{REF} + 0.09	1.418
HSTL12I	1.14	1.2	1.26	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	1.26
HSTL12II	1.14	1.2	1.26	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	1.26
HSUL18I	1.71	1.8	1.89	–0.3	0.3 × V_{DDI}	0.7 × V_{DDI}	1.89
HSUL18II	1.71	1.8	1.89	–0.3	0.3 × V_{DDI}	0.7 × V_{DDI}	1.89
HSUL12I	1.14	1.2	1.26	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	1.26
POD12I	1.14	1.2	1.26	–0.3	V_{REF} – 0.08	V_{REF} + 0.08	1.26
POD12II	1.14	1.2	1.26	–0.3	V_{REF} – 0.08	V_{REF} + 0.08	1.26

1. GPIO V_{IH} max is 3.45 V with PCI clamp diode turned off regardless of mode, that is, over-voltage tolerant.
2. For external stub-series resistance. This resistance is on-die for GPIO.

Note: 3.3 V and 2.5 V are only supported in GPIO banks.

Table 13 • DC Output Levels

I/O Standard	V_{DDI} Min (V)	V_{DDI} Typ (V)	V_{DDI} Max (V)	V_{OL} Min (V)	V_{OL} Max (V)	V_{OH} Min (V)	V_{OH} Max (V)	I_{OL}[2,6] mA	I_{OH}[2,6] mA
PCI[1]	3.15	3.3	3.45		0.1 × V_{DDI}	0.9 × V_{DDI}		1.5	0.5
LVTTL	3.15	3.3	3.45		0.4	2.4			
LVCMOS33	3.15	3.3	3.45		0.4	V_{DDI} – 0.4			
LVCMOS25	2.375	2.5	2.625		0.4	V_{DDI} – 0.4			
LVCMOS18	1.71	1.8	1.89		0.45	V_{DDI} – 0.45			
LVCMOS15	1.425	1.5	1.575		0.25 × V_{DDI}	0.75 × V_{DDI}			
LVCMOS12	1.14	1.2	1.26		0.25 × V_{DDI}	0.75 × V_{DDI}			
SSTL25I[3]	2.375	2.5	2.625		V_{TT} – 0.608	V_{TT} + 0.608		8.1	8.1
SSTL25II[3]	2.375	2.5	2.625		V_{TT} – 0.810	V_{TT} + 0.810		16.2	16.2
SSTL18I[3]	1.71	1.8	1.89		V_{TT} – 0.603	V_{TT} + 0.603		6.7	6.7
SSTL18II[3]	1.71	1.8	1.89		V_{TT} – 0.603	V_{TT} + 0.603		13.4	13.4
SSTL15I[4]	1.425	1.5	1.575		0.2 × V_{DDI}	0.8 × V_{DDI}		V_{OL}/40	(V_{DDI} – V_{OH}) /40
SSTL15II[4]	1.425	1.5	1.575		0.2 × V_{DDI}	0.8 × V_{DDI}		V_{OL}/34	(V_{DDI} – V_{OH}) /34
SSTL135I[4]	1.283	1.35	1.418		0.2 × V_{DDI}	0.8 × V_{DDI}		V_{OL}/40	(V_{DDI} – V_{OH}) /40
SSTL135II[4]	1.283	1.35	1.418		0.2 × V_{DDI}	0.8 × V_{DDI}		V_{OL}/34	(V_{DDI} – V_{OH}) /34
HSTL15I	1.425	1.5	1.575		0.4	V_{DDI} – 0.4		8	8
HSTL15II	1.425	1.5	1.575		0.4	V_{DDI} – 0.4		16	16

I/O Standard	Bank Type	V_{OCM}[1] Min (V)	V_{OCM} Typ (V)	V_{OCM} Max (V)	V_{OD}[2] Min (V)	V_{OD}[2] Typ (V)	V_{OD}[2] Max (V)
MLVDSE25[3]	GPIO		1.25		0.396	0.442	0.453
LVPECLE33[3]	GPIO		1.65		0.664	0.722	0.755
MIPIE25[3]	GPIO		0.25		0.1	0.22	0.3

1. V_{OCM} is the output common mode voltage.
2. V_{OD} is the output differential voltage.
3. Emulated output only.

6.3.3 Complementary Differential DC Input and Output Levels

The following tables list the complementary differential DC I/O levels.

Table 16 • Complementary Differential DC Input Levels

I/O Standard	V_{DDI} Min (V)	V_{DDI} Typ (V)	V_{DDI} Max (V)	V_{ICM}[1,3] Min (V)	V_{ICM}[1,3] Typ (V)	V_{ICM}[1,3] Max (V)	V_{ID}[2] Min (V)	V_{ID} Max (V)
SSTL25I	2.375	2.5	2.625	1.164	1.250	1.339	0.1	
SSTL25II	2.375	2.5	2.625	1.164	1.250	1.339	0.1	
SSTL18I	1.71	1.8	1.89	0.838	0.900	0.964	0.1	
SSTL18II	1.71	1.8	1.89	0.838	0.900	0.964	0.1	
SSTL15I	1.425	1.5	1.575	0.698	0.750	0.803	0.1	
SSTL15II	1.425	1.5	1.575	0.698	0.750	0.803	0.1	
SSTL135I	1.283	1.35	1.418	0.629	0.675	0.723	0.1	
SSTL135II	1.283	1.35	1.418	0.629	0.675	0.723	0.1	
HSTL15I	1.425	1.5	1.575	0.698	0.750	0.803	0.1	
HSTL15II	1.425	1.5	1.575	0.698	0.750	0.803	0.1	
HSTL135I	1.283	1.35	1.418	0.629	0.675	0.723	0.1	
HSTL135II	1.283	1.35	1.418	0.629	0.675	0.723	0.1	
HSTL12I	1.14	1.2	1.26	0.559	0.600	0.643	0.1	
HSUL18I	1.71	1.8	1.89	0.838	0.900	0.964	0.1	
HSUL18II	1.71	1.8	1.89	0.838	0.900	0.964	0.1	
HSUL12I	1.14	1.2	1.26	0.559	0.600	0.643	0.1	
POD12I	1.14	1.2	1.26	0.787	0.840	0.895	0.1	
POD12II	1.14	1.2	1.26	0.787	0.840	0.895	0.1	

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage.
3. V_{ICM} rules are as follows:
   a. V_{ICM} must be less than V_{DDI} -0.4V;
   b. $V_{ICM} + V_{ID}/2$ must be $<V_{DDI} + 0.4$ V;
   c. $V_{ICM} – V_{ID}/2$ must be >VSS – 0.3 V.

7.1.6 User I/O Switching Characteristics

The following section describes characteristics for user I/O switching.

For more information about user I/O timing, see the *PolarFire I/O Timing Spreadsheet* (to be released).

7.1.6.1 I/O Digital

The following tables provide information about I/O digital.

Table 30 • I/O Digital Receive Single-Data Rate Switching Characteristics

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit	Clock-to-Data Condition
FMAX	RX_SDR_G_A	Rx SDR							MHz	From a global clock source, aligned
FMAX	RX_SDR_L_A	Rx SDR							MHz	From a lane clock source, aligned
FMAX	RX_SDR_G_C	Rx SDR							MHz	From a global clock source, centered
FMAX	RX_SDR_L_C	Rx SDR							MHz	From a lane clock source, centered

Table 31 • I/O Digital Receive Double-Data Rate Switching Characteristics

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit	Clock-to-Data Condition
FMAX	RX_DDR_G_A	Rx DDR		335			335	MHz	MHz	From a global clock source, aligned
FMAX	RX_DDR_L_A	Rx DDR		250			250		MHz	From a lane clock source, aligned
FMAX	RX_DDR_G_C	Rx DDR		335			335		MHz	From a global clock source, centered
FMAX	RX_DDR_L_C	Rx DDR		250			250		MHz	From a lane clock source, centered
FMAX 2:1	RX_DDRX_B_A	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit	Clock-to-Data Condition
FMAX 8:1	RX_DDRX_BL_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered

Table 32 • I/O Digital Transmit Single-Data Rate Switching Characteristics

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit	Forwarded Clock-to-Data Skew
Output FMAX	TX_SDR_G_A	Tx SDR							MHz	From a global clock source, aligned[1]
	TX_SDR_G_C	Tx SDR							MHz	From a global clock source, centered[1]

1. A centered clock-to-data interface can be created with a negedge launch of the data.

Table 33 • I/O Digital Transmit Double-Data Rate Switching Characteristics

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit	Forwarded Clock-to-Data Skew
Output FMAX	TX_DDR_G_A	Tx DDR			335			335	MHz	From a global clock source, aligned
	TX_DDR_G_C	Tx DDR			335			335	MHz	From a global clock source, centered
	TX_DDR_L_A	Tx DDR			250			250	MHz	From a lane clock source, aligned
	TX_DDR_L_C	Tx DDR			250			250	MHz	From a lane clock source, centered
Output FMAX 2:1	TX_DDRX_B_A	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
Output FMAX 4:1	TX_DDRX_B_A	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
Output FMAX 8:1	TX_DDRX_B_A	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned

Parameter	Symbol	V_{DD} = 1.0 V STD	V_{DD} = 1.0 V –1	V_{DD} = 1.05 V STD	V_{DD} = 1.05 V –1	Unit	Condition
Regional clock duty cycle distortion	T_{DCDR}	120	120	120	120	ps	At 250 MHz

The following table provides clocking specifications from –40 °C to 100 °C.

Table 36 • High-Speed I/O Clock Characteristics (–40 °C to 100 °C)

Parameter	Symbol	V_{DD} = 1.0 V STD	V_{DD} = 1.0 V –1	V_{DD} = 1.05 V STD	V_{DD} = 1.05 V –1	Unit	Condition
High-speed I/O clock F_{MAX}	F_{MAXB}	1000	1250	1000	1250	MHz	HSIO and GPIO
High-speed I/O clock skew[1]	F_{SKEWB}	30	20	30	20	ps	HSIO without bridging
	F_{SKEWB}	600	500	600	500	ps	HSIO with bridging
	F_{SKEWB}	45	35	45	35	ps	GPIO without bridging
	F_{SKEWB}	75	60	75	60	ps	GPIO with bridging
High-speed I/O clock duty cycle distortion[2]	T_{DCB}	90	90	90	90	ps	HSIO without bridging
	T_{DCB}	115	115	115	115	ps	HSIO with bridging
	T_{DCB}	90	90	90	90	ps	GPIO without bridging
	T_{DCB}	115	115	115	115	ps	GPIO with bridging

1. F_{SKEWB} is the worst-case clock-tree skew observable between sequential I/O elements. Clock-tree skew is significantly smaller at I/O registers close to each other and fed by the same or adjacent clock-tree branches. Use the Microsemi Timing Analyzer tool to evaluate clock skew specific to the design.
2. Parameters listed in this table correspond to the worst-case duty cycle distortion observable at the I/O flip flops. IBIS should be used to calculate any additional duty cycle distortion that might be caused by asymmetrical rise/fall times for any I/O standard.

7.2.2 PLL

The following table provides information about PLL.

Table 37 • PLL Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Input clock frequency (integer mode)	F_{INI}	1		1250	MHz
Input clock frequency (fractional mode)	F_{INF}	10		1250	MHz
Minimum reference or feedback pulse width[1]	$F_{INPULSE}$	200			ps
Frequency at the Frequency Phase Detector (PFD) (integer mode)	F_{PHDETI}	1		312	MHz
Frequency at the PFD (fractional mode)	F_{PHDETF}	10	50	125	MHz
Allowable input duty cycle	F_{INDUTY}	25		75	%

Parameter[1]	Symbol	Min	Typ	Max	Unit
Secondary output clock frequency[2]	F_{OUTSF}	33.3		800	MHz
Input clock cycle-to-cycle jitter	F_{INJ}			200	ps
Output clock period cycle-to-cycle jitter (w/clean input)	$T_{OUTJITTERP}$			300	ps
Output clock-to-clock skew between two outputs with the same phase settings	T_{SKEW}			±200	ps
DLL lock time	T_{LOCK}	16		16K	Reference clock cycles
Minimum reset pulse width	T_{MRPW}	3			ns
Minimum input pulse width[3]	T_{MIPW}	20			ns
Minimum input clock pulse width high	T_{MPWH}	400			ps
Minimum input clock pulse width low	T_{MPWL}	400			ps
Delay step size	T_{DEL}	12.7	30	35	ps
Maximum delay block delay[4]	T_{DELMAX}	1.8		4.8	ns
Output clock duty cycle (with 50% duty cycle input)[5]	T_{DUTY}	40		60	%
Output clock duty cycle (in phase reference mode)[5]	T_{DUTY50}	45		55	%

1. For all DLL modes.
2. Secondary output clock divided by four option.
3. On load, direction, move, hold, and update input signals.
4. 128 delay taps in one delay block.
5. Without duty cycle correction enabled.

7.2.4 RC Oscillators

The following tables provide internal RC clock resources for user designs and additional information about designing systems with RF front end information about emitters generated on-chip to support programming operations.

Table 39 • 2 MHz RC Oscillator Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Operating frequency	RC_{2FREQ}		2		MHz
Accuracy	RC_{2FACC}	–4		4	%
Duty cycle	RC_{2DC}	46		54	%
Peak-to-peak output period jitter	RC_{2PJIT}		5	10	ns
Peak-to-peak output cycle-to-cycle jitter	RC_{2CJIT}		5	10	ns
Operating current (V_{DD25})	RC_{2IVPPA}			60	µA
Operating current (V_{DD})	RC_{2IVDD}			2.6	µA

Table 40 • 160 MHz RC Oscillator Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Operating frequency	RC_{SCFREQ}		160		MHz
Accuracy	RC_{SCFACC}	–4		4	%
Duty cycle	RC_{SCDC}	47		52	%
Peak-to-peak output period jitter	RC_{SCPJIT}			600	ps
Peak-to-peak output cycle-to-cycle jitter	RC_{SCCJIT}			172	ps
Operating current (V_{DD25})	RC_{SCVPPA}			599	µA

7.3 Fabric Specifications

The following section describes specifications for the fabric.

7.3.1 Math Blocks

The following tables describe math block performance.

Table 41 • Math Block Performance Extended Commercial Range (0 °C to 100 °C)

Parameter	Symbol	Modes	V_{DD} = 1.0 V – STD	V_{DD} = 1.0 V – 1	V_{DD} = 1.05 V – STD	V_{DD} = 1.05 V – 1	Unit
Maximum operating frequency	F_{MAX}	18 × 18 multiplication	370	470	440	500	MHz
		18 × 18 multiplication summed with 48-bit input	370	470	440	500	MHz
		18 × 19 multiplier pre-adder ROM mode	365	465	435	500	MHz
		Two 9 × 9 multiplication	370	470	440	500	MHz
		9 × 9 dot product (DOTP)	370	470	440	500	MHz
		Complex 18 × 19 multiplication	360	455	430	500	MHz

Table 42 • Math Block Performance Industrial Range (–40 °C to 100 °C)

Parameter	Symbol	Modes	V_{DD} = 1.0 V – STD	V_{DD} = 1.0 V – 1	V_{DD} = 1.05 V – STD	V_{DD} = 1.05 V – 1	Unit
Maximum operating frequency	F_{MAX}	18 × 18 multiplication	365	465	435	500	MHz
		18 × 18 multiplication summed with 48-bit input	365	465	435	500	MHz
		18 × 19 multiplier pre-adder ROM mode	355	460	430	500	MHz
		Two 9 × 9 multiplication	365	465	435	500	MHz
		9 × 9 DOTP	365	465	435	500	MHz
		Complex 18 × 19 multiplication	350	450	425	500	MHz

Table 44 • µSRAM Performance

Parameter	Symbol	V_{DD} = 1.0 V – STD	V_{DD} = 1.0 V – 1	V_{DD} = 1.05 V – STD	V_{DD} = 1.05 V – 1	Unit	Condition
Operating frequency	F_{MAX}	400	415	450	480	MHz	Write-port
Read access time	Tac		2		2	ns	Read-port

Table 45 • µPROM Performance

Parameter	Symbol	V_{DD} = 1.0 V – STD	V_{DD} = 1.0 V – 1	V_{DD} = 1.05 V – STD	V_{DD} = 1.05 V – 1	Unit
Read access time	Tac	10	10	10	10	ns

7.4 Transceiver Switching Characteristics

This section describes transceiver switching characteristics.

7.4.1 Transceiver Performance

The following table describes transceiver performance.

Table 46 • PolarFire Transceiver and TXPLL Performance

Parameter	Symbol	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit
Tx data rate[1,2]	F_{TXRate}	0.25		10.3125	0.25		12.7	Gbps
Tx OOB (serializer bypass) data rate	$F_{TXRateOOB}$	DC		1.5	DC		1.5	Gbps
Rx data rate when AC coupled[2]	$F_{RxRateAC}$	0.25		10.3125	0.25		12.7	Gbps
Rx data rate when DC coupled	$F_{RxRateDC}$	0.25		3.2	0.25		3.2	Gbps
Rx OOB (deserializer bypass) data rate	$F_{TXRateOOB}$	DC		1.25	DC		1.25	Gbps
TXPLL output frequency[3]	F_{TXPLL}	1.6		6.35	1.6		6.35	GHz
Rx CDR mode	F_{RXCDR}	0.25		10.3125	0.25		10.3125	Gbps
Rx DFE mode[2]	F_{RXDFE}	3.0		10.3125	3.0		12.7	Gbps
Rx Eye Monitor mode[2]	$F_{RXEyeMon}$	3.0		10.3125	3.0		12.7	Gbps

1. The reference clock is required to be a minimum of 75 MHz for data rates of 10 Gbps and above.
2. For data rates greater than 10.3125 Gbps, VDDA must be set to 1.05 V mode. See supply tolerance in the section Recommended Operating Conditions (see page 6).
3. The Tx PLL rate is between 0.5x to 5.5x the Tx data rate. The Tx data rate depends on per XCVR lane Tx post-divider settings.

7.4.2 Transceiver Reference Clock Performance

The following table describes performance of the transceiver reference clock.

Table 47 • PolarFire Transceiver Reference Clock AC Requirements

Parameter	Symbol	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit
Reference clock input rate[1, 2]	$F_{TXREFCLK}$	20		800	20		800	MHz

5. Improved jitter characteristics for a specific industry standard are possible in many cases due to improved reference clock or higher V_{CO} rate used.
6. Tx jitter is specified with all transmitters on the device enabled, a 10–12-bit error rate (BER) and Tx data pattern of PRBS7.
7. From the PMA mode, the TX_ELEC_IDLE port to the XVCR TXP/N pins.
   FTxRefClk = 75 MHz with typical settings.
   For data rates greater than 10.3125 Gbps, VDDA must be set to 1.05 V mode. See supply tolerance in the section Recommended Operating Conditions (see page 6). (see page 6)

7.4.6 Receiver Performance

The following table describes performance of the receiver.

Table 53 • PolarFire Transceiver Receiver Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Input voltage range	V_{IN}	0		V_{DDA} + 0.3	V	
Differential peak-to-peak amplitude	V_{IDPP}	140		1250	mV	
Differential termination	V_{ITERM}		85		Ω	
	V_{ITERM}		100		Ω	
	V_{ITERM}		150		Ω	
Common mode voltage	V_{ICMDC} [1]	0.7 × V_{DDA}		0.9 × V_{DDA}	V	DC coupled
Exit electrical idle detection time	T_{EIDET}		50	100	ns	
Run length of consecutive identical digits (CID)	C_{ID}			200	UI	
CDR PPM tolerance[2]	C_{DRPPM}			1.15	% UI	
CDR lock-to-data time	T_{LTD}				CDR_{REFCLK} UI	
CDR lock-to-ref time	T_{LTF}				CDR_{REFCLK} UI	
Loss-of-signal detect (Peak Detect Range setting = high)[9]	$V_{DETLHIGH}$				mV	Setting = 1
	$V_{DETLHIGH}$				mV	Setting = 2
	$V_{DETLHIGH}$				mV	Setting = 3
	$V_{DETLHIGH}$				mV	Setting = 4
	$V_{DETLHIGH}$				mV	Setting = 5
	$V_{DETLHIGH}$				mV	Setting = 6
	$V_{DETLHIGH}$				mV	Setting = 7
Loss-of-signal detect (Peak Detect Range setting = low)[9]	V_{DETLOW}	65		175	mV	Setting = PCIe[3,7]
	V_{DETLOW}	95		190	mV	Setting = SATA[4,8]
	V_{DETLOW}	75		170	mV	Setting = 1
	V_{DETLOW}	95		185	mV	Setting = 2
	V_{DETLOW}	100		190	mV	Setting = 3
	V_{DETLOW}	140		210	mV	Setting = 4
	V_{DETLOW}	155		240	mV	Setting = 5
	V_{DETLOW}	165		245	mV	Setting = 6
	V_{DETLOW}	170		250	mV	Setting = 7
Sinusoidal jitter tolerance	T_{SJTOL}				UI	>8.5 Gbps – 12.7 Gbps [5, 10]

Parameter	Symbol	Min	Typ	Max	Unit	Condition
		0.41			UI	>3.2–8.5 Gbps[5]
		0.41			UI	>1.6 to 3.2 Gbps[5]
		0.41			UI	>0.8 to 1.6 Gbps [5]
		0.41			UI	250 to 800 Mpbs [5]
Total jitter tolerance with stressed eye	$T_{TJTOLSE}$	0.65			UI	3.125 Gbps[5]
		0.65			UI	6.25 Gbps[6]
		0.7			UI	10.3125 Gbps[6]
					UI	12.7 Gbps[6, 10]
Sinusoidal jitter tolerance with stressed eye	$T_{SJTOLSE}$	0.1			UI	3.125 Gbps[5]
		0.05			UI	6.25 Gbps[6]
		0.05			UI	10.3125 Gbps[6]
					UI	12.7 Gbps[6, 10]
CTLE DC gain (all stages, max settings)				10	dB	
CTLE AC gain (all stages, max settings)				16	dB	
DFE AC gain (per 5 stages, max settings)				7.5	dB	

1. Valid at 3.2 Gbps and below.
2. Data vs. Rx reference clock frequency.
3. Achieves compliance with PCIe electrical idle detection.
4. Achieves compliance with SATA OOB specification.
5. Rx jitter values based on bit error ratio (BER) of 10–12, AC coupled input with 400 mV V_{ID}, all stages of Rx CTLE enabled, DFE disabled, 80 MHz sinusoidal jitter injected to Rx data.
6. Rx jitter values based on bit error ratio (BER) of 10–12, AC coupled input with 400 mV V_{ID}, all stages of Rx CTLE enabled, DFE enabled, 80 MHz sinusoidal jitter injected to Rx data.
7. For PCIe: Low Threshold Setting = 1, High Threshold Setting = 2.
8. For SATA: Low Threshold Setting = 2, High Threshold Setting = 3.
9. Loss of signal detection is valid for input signals that transition at a density ≥1 Gbps for PRBS7 data or 6 Gbps for PRBS31 data.
10. For data rates greater than 10.3125 Gbps, VDDA must be set to 1.05 V mode. See supply tolerance in the section Recommended Operating Conditions (see page 6).

7.5 Transceiver Protocol Characteristics

The following section describes transceiver protocol characteristics.

7.5.1 PCI Express

The following tables describe the PCI express.

Table 54 • PCI Express Gen1

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	2.5 Gbps		0.25	UI
Receiver jitter tolerance	2.5 Gbps	0.4		UI

Note: With add-in card, as specified in PCI Express CEM Rev 2.0.

Table 75 • FPGA Programming Cycles Lifetime Factor

Programming T_J	Programming Cycles	LF
–40 °C to 100 °C	500	1
–40 °C to 85 °C	1000	0.8
–40 °C to 55 °C	2000	0.6

Notes:

- The maximum number of device digest cycles is 100K.
- Digests are operational only over the –40 °C to 100 °C temperature range.
- After a program cycle, an additional N digests cycles are allowed with the resultant retention characteristics for the total operating and storage temperature shown.
- Retention is specified for total device storage and operating temperature.
- All temperatures are junction temperatures (T_J).
- Example 1—500 digests cycles are performed between programming cycles. N = 500. The operating conditions are –40 °C to 85 °C T_J. 501 programming cycles have occurred. The retention under these operating conditions is 20 × LF = 20 × .8 = 16 years.
- Example 2—one programming cycle has occurred, N = 1500 digest cycles have occurred. Temperature range is –40 °C to 100 °C. The resultant retention is 10 × LF or 10 years over the industrial temperature range.

7.6.5 Digest Time

The following table describes digest time.

Table 76 • Digest Times

Parameter	Devices	Typ	Max	Unit
Setup time	All	2		µs
Fabric digest run time	MPF100T, TL, TS, TLS			ms
	MPF200T, TL, TS, TLS	1005	1072	ms
	MPF300T, TL, TS, TLS	1503.9	1582	ms
	MPF500T, TL, TS, TLS			ms
UFS CC digest run time	MPF100T, TL, TS, TLS			µs
	MPF200T, TL, TS, TLS	33.2	35	µs
	MPF300T, TL, TS, TLS	33.2	35	µs
	MPF500T, TL, TS, TLS			µs
sNVM digest run time[1]	MPF100T, TL, TS, TLS			ms
	MPF200T, TL, TS, TLS	4.4	4.8	ms
	MPF300T, TL, TS, TLS	4.4	4.8	ms
	MPF500T, TL, TS, TLS			ms
UFS UL digest run time	MPF100T, TL, TS, TLS			µs
	MPF200T, TL, TS, TLS	46.6	48.8	µs
	MPF300T, TL, TS, TLS	46.6	48.8	µs
	MPF500T, TL, TS, TLS			µs
User key digest run time[2]	MPF100T, TL, TS, TLS			µs
	MPF200T, TL, TS, TLS	525.4	543.3	µs
	MPF300T, TL, TS, TLS	525.4	543.3	µs
	MPF500T, TL, TS, TLS			µs

Parameter	Devices	Typ	Max	Unit
UFS UPERM digest run time	MPF100T, TL, TS, TLS			µs
	MPF200T, TL, TS, TLS	33.2	34.9	µs
	MPF300T, TL, TS, TLS	33.2	34.9	µs
	MPF500T, TL, TS, TLS			µs
Factory digest run time	MPF100T, TL, TS, TLS			µs
	MPF200T, TL, TS, TLS	493.6	510.1	µs
	MPF300T, TL, TS, TLS	493.6	510.1	µs
	MPF500T, TL, TS, TLS			µs

1. The entire sNVM is used as ROM.
2. Valid for user key 0 through 6.

Note: These times do not include the power-up to functional timing overhead when using digest checks on power-up.

7.6.6 Zeroization Time

The following tables describe zeroization time. A zeroization operation is counted as one programming cycle.

Table 77 • Zeroization Times for MPF100T, TL, TS, and TLS Devices

Parameter	Typ	Max	Unit	Conditions
Time to enter zeroization			ms	Zip flag set
Time to destroy the fabric data[1]			ms	Data erased
Time to destroy data in non-volatile memory (like new)[1, 2]			ms	One iteration of scrubbing
Time to destroy data in non-volatile memory (recoverable)[1, 3]			ms	One iteration of scrubbing
Time to destroy data in non-volatile memory (non-recoverable)[1, 4]			ms	One iteration of scrubbing
Time to scrub the fabric data[1]			s	Full scrubbing
Time to scrub the pNVM data (like new)[1, 2]			s	Full scrubbing
Time to scrub the pNVM data (recoverable)[1, 3]			s	Full scrubbing
Time to scrub the fabric data pNVM data (non-recoverable)[1, 4]			s	Full scrubbing
Time to verify[5]			s	

1. Total completion time after entering zeroization.
2. Like new mode—zeroizes user design security setting and sNVM content.
3. Recoverable mode—zeroizes user design security setting, sNVM and factory keys.
4. Non-recoverable mode—zeroizes user design security setting, sNVM and factory keys, and factory data required for programming.
5. Time to verify after scrubbing completes.

Table 78 • Zeroization Times for MPF200T, TL, TS, and TLS Devices

Parameter	Typ	Max	Unit	Conditions
Time to enter zeroization			ms	Zip flag set
Time to destroy the fabric data[1]			ms	Data erased
Time to destroy data in non-volatile memory (like new)[1, 2]			ms	One iteration of scrubbing

Devices	IAP	FlashPro4	FlashPro5	BP	Silicon Sculptor	Units
MPF500T, TL, TS, TLS						

Notes:

- FlashPro4 4 MHz TCK.
- FlashPro5 10 MHz TCK.
- PC configuration: Intel i7 at 3.6 GHz, 32 GB RAM, Windows 10.

Table 83 • Verify System Services

Parameter	Symbol	ServiceID	Devices	Typ	Max	Unit
In application verify by index	$T_{IAP\_Ver\_Index}$	44H	MPF100T, TL, TS, TLS			s
			MPF200T, TL, TS, TLS	8.2	9	s
			MPF300T, TL, TS, TLS	12.4	13	s
			MPF500T, TL, TS, TLS			s
In application verify by SPI address	$T_{IAP\_Ver\_Addr}$	45H	MPF100T, TL, TS, TLS			s
			MPF200T, TL, TS, TLS	8.2	9	s
			MPF300T, TL, TS, TLS	12.4	13	s
			MPF500T, TL, TS, TLS			s

7.6.8 Authentication Time

The following tables describe authentication system service time.

Table 84 • Authentication Services

Parameter	Symbol	ServiceID	Devices	Typ	Max	Unit
Bitstream Authentication	T_{BIT_AUTH}	22H	MPF100T, TL, TS, TLS			s
			MPF200T, TL, TS, TLS	3.3	3.7	s
			MPF300T, TL, TS, TLS	4.9	5.4	s
			MPF500T, TL, TS, TLS			s
IAP Image Authentication	T_{IAP_AUTH}	23H	MPF100T, TL, TS, TLS			s
			MPF200T, TL, TS, TLS	3.3	3.7	s
			MPF300T, TL, TS, TLS	4.9	5.4	s
			MPF500T, TL, TS, TLS			

7.6.9 Secure NVM Performance

The following table describes secure NVM performance.

Table 85 • sNVM Read/Write Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Plain text programming		7.0	7.2	7.9	ms	
Authenticated text programming		7.2	7.4	9.4	ms	
Authenticated and encrypted text programming		7.2	7.4	9.4	ms	
Authentication R/W 1st access from power-up overhead	T_{PUF_OVHD}		100	111	ms	From T_{FAB_READY}
Plain text read		7.67	7.79	8.2	µs	

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Authenticated text read		113.25	114.02	118.5	µs	
Authenticated and decrypted text read		159.59	160.53	166.5	µs	

Notes:

- Page size= 252 bytes (non-authenticated), 236 bytes (authenticated).
- Only page reads and writes allowed.
- T_{PUF_OVHD} is an additional time that occurs on the first R/W, after cold or warm boot, to sNVM using authenticated or authenticated and encrypted text.

7.6.10 Secure NVM Programming Cycles

The following table describes secure NVM programming cycles.

Table 86 • sNVM Programming Cycles vs. Retention Characteristics

Programming Temperature	Programming Cycles per Page, Max	Programming Cycles per Block, Max	Retention Years
–40 °C to 100 °C	10,000	100,000	20
–40 °C to 85 °C	10,000	100,000	20
–40 °C to 55 °C	10,000	100,000	20

Note: Page size = 128 bytes. Block size = 56 KBytes.

7.7 System Services

This section describes system switching and throughput characteristics.

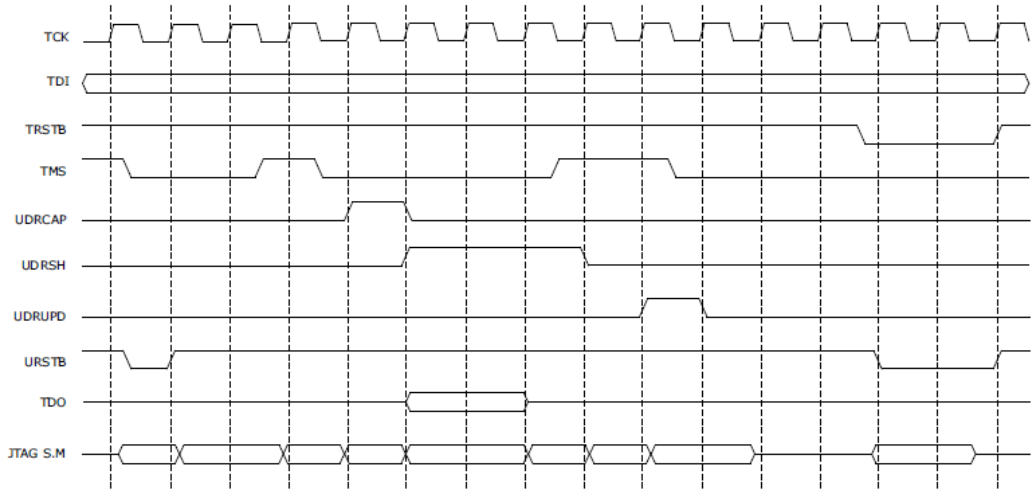
7.7.1 System Services Throughput Characteristics

The following table describes system services throughput characteristics.

Table 87 • System Services Throughput Characteristics

Parameter	Symbol	Service ID	Typ	Max	Unit	Conditions
Serial number	T_{Serial}	00H	65	67	µs	
User code	T_{User}	01H	0.8	1.05	µs	
Design information	T_{Design}	02H	2.4	2.7	µs	
Device certificate	T_{Cert}	03H	255	271	ms	
Read digests	T_{digest_read}	04H	201	215	µs	
Query security locks	T_{sec_Query}	05H	15	17	µs	
Read debug information	T_{Rd_debug}	06H	34	38	µs	
Reserved		07H–0FH				
Secure NVM write plain text	$T_{SNVM\_Wr\_Plain}$	10H				Note 1
Secure NVM write authenticated plain text	$T_{SNVM\_Wr\_Auth}$	11H				Note 1
Secure NVM write authenticated cipher text	$T_{SNVM\_Wr\_Cipher}$	12H				Note 1
Reserved		13H–17H				

Figure 3 • UJTAG Timing Diagram



7.8.2 UJTAG_SEC Switching Characteristics

The following table describes characteristics of UJTAG_SEC switching.

Table 89 • UJTAG Security Performance Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
TCK frequency	F_{TCK}				MHz	

7.8.3 USPI Switching Characteristics

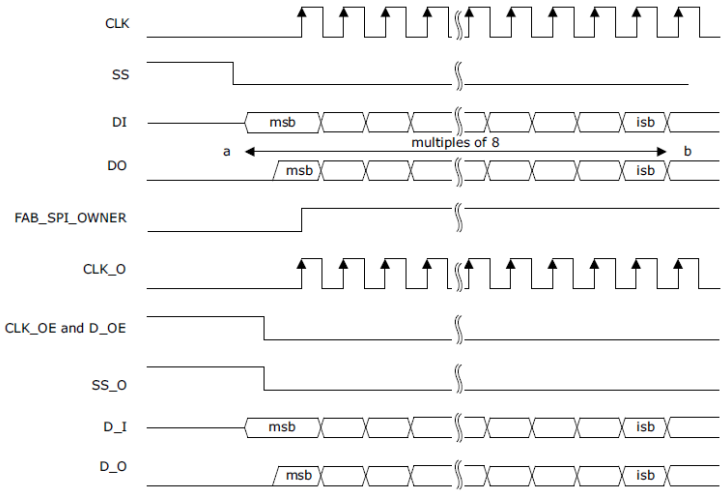
The following section describes characteristics of USPI switching.

Table 90 • SPI Macro Interface Timing Characteristics

Parameter	Symbol	V_{DDI} = 3.3 V Max	V_{DDI} = 2.5 V Max	V_{DDI} = 1.8 V Max	V_{DDI} = 1.5 V Max	V_{DDI} = 1.2 V Max	Unit
Propagation delay from the fabric to pins[1]	TPD_MOSI	0.8	1	1.2	1.4	1.6	ns
	TPD_MISO	3.5	3.75	4	4.25	4.5	ns
	TPD_SS	3.5	3.75	4	4.25	4.5	ns
	TPD_SCK	3.5	3.75	4	4.25	4.5	ns
	TPD_MOSI_OE	3.5	3.75	4	4.25	4.5	ns
	TPD_SS_OE	3.5	3.75	4	4.25	4.5	ns
	TPD_SCK_OE	3.5	3.75	4	4.25	4.5	ns

1. Assumes CL of the relevant I/O standard as described in the input and output delay measurement tables.

Figure 4 • USPI Switching Characteristics



7.8.4 Tamper Detectors

The following section describes tamper detectors.

Table 91 • ADC Conversion Rate

Parameter	Description	Min	Typ[1]	Max
T_{CONV1}	Time from enable changing from zero to non-zero value to first conversion completes. Minimum value applies when POWEROFF = 0.	420 µs		470 µs
T_{CONVN}	Time between subsequent channel conversions.		480 µs	
T_{SETUP}	Data channel and output to valid asserted. Data is held until next conversion completes, that is >480 µs.	0 ns		
T_{VALID}[2]	Width of the valid pulse.	1.625 µs		2 µs
T_{RATE}	Time from start of first set of conversions to the start of the next set. Can be considered as the conversion rate. Is set by the conversion rate parameter.	480 µs	Rate × 32 µs	8128 µs

1. Min, typ, and max refer to variation due to functional configuration and the raw TVS value. The actual internal correction time will vary based on the raw TVS value.
2. The pulse width varies depending on the time taken to complete the internal calibration multiplication, this can be up to 375 ns.

Note: Once the TVS block is active, the enable signal is sampled 25 ns before the falling edge of valid. The next enabled channel in the sequence 0-1-2-3 is started; that is, if channel 0 has just completed and only channels 0 and 3 are enabled, the next channel will be 3. When all the enabled channels in the sequence 0-1-2-3 are completed, the TVS waits for the conversion rate timer to expire. The enable signal may be changed at any time if it changes to 4'b0000 while valid is asserted (and 25 ns before valid is de-asserted), then no further conversions will be started.

Table 92 • Temperature and Voltage Sensor Electrical Characteristics

Parameter	Min	Typ	Max	Unit	Condition
Temperature sensing range	–40		125	°C	
Temperature sensing accuracy	–10		10	°C	

7.9.4 Design Dependence of T PUFT and T WRFT

Some phases of the device initialization are user design-dependent, as the device automatically initializes certain resources to user-specified configurations if those resources are used in the design. It is necessary to compute the overall power-up to functional time by referencing the following tables and adding the relevant phases, according to the design configuration. The following equation refers to timing parameters specified in the above timing diagrams. Please note T_{PCIE} , T_{XCVR}, T_{LSRAM}, and T_{USRAM} can be found in the PolarFire FPGA device power-up and resets user guide UG0725.

$T_{PUFT} = T_{FAB\_READY(cold)} + \max((T_{PCIE} + T_{XCVR} + T_{LSRAM} + T_{USRAM}), T_{CALIB})$

$T_{WRFT} = T_{FAB\_READY(warm)} + \max((T_{PCIE} + T_{XCVR} + T_{LSRAM} + T_{USRAM}), T_{CALIB})$

Note: T_{PCIE}, T_{XCVR}, T_{LSRAM}, T_{USRAM}, and T_{CALIB} are common to both cold and warm reset scenarios.

Auto-initialization of FPGA (if required) occurs in parallel with I/O calibration. The device may be considered fully functional only when the later of these two activities has finished, which may be either one, depending on the configuration, as may be calculated from the following tables. Note that I/O calibration may extend beyond T_{PUFT} (as I/O calibration process is independent of main device power-on and is instead dependent on I/O bank supply relative power-on time and ramp times). The previous timing diagram for power-on initialization shows the earliest that I/Os could be enabled, if the I/O power supplies are powered on before or at the same time as the main supplies.

7.9.5 Cold Reset to Fabric and I/Os (Low Speed) Functional

The following table specifies the minimum, typical, and maximum times from the power supplies reaching the above trip point levels until the FPGA fabric is operational and the FPGA IOs are functional for low-speed (sub 400 MHz) operation.

Table 99 • Cold Boot

Power-On (Cold) Reset to Fabric and I/O Operational	Min	Typ	Max	Unit
Time when input pins start working – $T_{IN\_ACTIVE(cold)}$	1.17	4.51	7.84	ms
Time when weak pull-ups are enabled – $T_{PU\_PD\_ACTIVE(cold)}$	1.17	4.51	7.84	ms
Time when fabric is operational – $T_{FAB\_READY(cold)}$	1.20	4.54	7.87	ms
Time when output pins start driving – $T_{OUT\_ACTIVE(cold)}$	1.22	4.56	7.89	ms

7.9.6 Warm Reset to Fabric and I/Os (Low Speed) Functional

The following table specifies the minimum, typical, and maximum times from the negation of the warm reset event until the FPGA fabric is operational and the FPGA IOs are functional for low-speed (sub 400 MHz) operation.

Table 100 • Warm Boot

Warm Reset to Fabric and I/O Operational	Min	Typ	Max	Unit
Time when input pins start working – $T_{IN\_ACTIVE(warm)}$	0.91	1.76	2.62	ms
Time when weak pull-ups/pull-downs are enabled – $T_{PU\_PD\_ACTIVE(warm)}$	0.91	1.76	2.62	ms
Time when fabric is operational – $T_{FAB\_READY(warm)}$	0.94	1.79	2.65	ms
Time when output pins start driving – $T_{OUT\_ACTIVE(warm)}$	0.96	1.81	2.67	ms

7.9.7 Miscellaneous Initialization Parameters

In the following table, T_{FAB_READY} refers to either $T_{FAB\_READY(cold)}$ or $T_{FAB\_READY(warm)}$ as specified in the previous tables, depending on whether the initialization is occurring as a result of a cold or warm reset, respectively.

1. With DPA counter measures.

Table 115 • HMAC

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
HMAC-SHA-256[1], 256-bit key	512	7477	2361
	64K	88367	2099
HMAC-SHA-384[1], 384-bit key	1024	13049	2257
	64K	106103	2153

1. With DPA counter measures.

Table 116 • CMAC

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
AES-CMAC-256[1] (message is only authenticated)	128	446	9058
	64K	45494	111053

1. With DPA counter measures.

Table 117 • KEY TREE

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
128-bit nonce + 8-bit optype		102457	2751
256-bit nonce + 8-bit optype		103218	2089

Table 118 • SHA

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
SHA-1[1]	512	2386	1579
	64K	77576	990
SHA-256[1]	512	2516	884
	64K	84752	938
SHA-384[1]	1024	4154	884
	64K	100222	938
SHA-512[1]	1024	4154	881
	64K	100222	935

1. With DPA counter measures.

Table 119 • ECC

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
ECDSA SigGen, P-384/SHA-384[1]	1024	12528912	6944
	8K	12540448	5643
ECDSA SigGen, P-384/SHA-384	1024	5502928	6155